

On pages 31-32, please replace the third full paragraph beginning at line 20 with the following:

Next, as shown in Fig. 3C, the protecting film 303 is removed, and activation of the added periodic table group V element is performed. A known technique of activation may be used as the means of activation, and activation is done in embodiment 1 by irradiation of excimer laser light. Both of pulse emission type laser and a continuous emission type laser may be used, and it is not necessary to place any limits on the use of excimer laser light. The goal is the activation of the added impurity element, and it is preferable that irradiation is performed at an energy level at which the crystallization silicon film does not melt. Note that the laser irradiation may also be performed with the protecting film 303 in place.

IN THE CLAIMS:

Please amended claims 1-5, 7, 10, 21, 30-35 as follows. While claims 1, 6, 11, 30, and 34 are presented below in their amended form, the amendments to the above-noted claims are outlined in an Attachment to the Amendment using the conventional indication method of bracketing and underlining.

1. (Amended) A method for manufacturing an electrical device, said method comprising the steps of:

- forming at least a thin film transistor on an insulating surface;
- forming an insulating film over the thin film transistor;
- forming a pixel electrode over the insulating film, said pixel electrode being connected to the thin film transistor;
- forming an EL layer over the pixel electrode;
- forming a second electrode over the EL layer,
- wherein the EL layer is selectively formed through an ink jet method,

wherein the insulating film comprises silicon,
wherein the insulating film is capable of preventing penetration of alkaline metal.

2. (Amended) A method for manufacturing an electrical device, said method comprising the steps of:

forming at least a thin film transistor;

forming an insulating film over the thin film transistor;

forming a pixel electrode over the insulating film, said pixel electrode being connected to the thin film transistor;

forming an EL layer over the pixel electrode;

forming a second electrode over the EL layer,

wherein the EL layer is selectively formed through an ink jet method

wherein the insulating film comprises aluminum oxide,

wherein the insulating film is capable of preventing penetration of alkaline metal.

3. (Amended) A method for manufacturing an electrical device, said method comprising the steps of:

forming at least a thin film transistor on an insulating surface;

forming an insulating film over the thin film transistor;

forming a pixel electrode over the insulating film, said pixel electrode being connected to the thin film transistor;

forming an EL layer over the pixel electrode;

forming a second electrode over the EL layer;

wherein the EL layer is selectively formed through an ink jet method,

wherein the insulating film comprises diamond like carbon,

wherein the insulating film is capable of preventing penetration of alkaline metal.

4. (Amended) A method for manufacturing an electrical device, said method comprising the steps of:

- forming at least a thin film transistor on an insulating surface;
- forming an insulating film over the thin film transistor;
- forming a pixel electrode over the insulating film, said pixel electrode being connected to the thin film transistor;
- forming an EL layer over the pixel electrode;
- forming a second electrode over the EL layer,

wherein the EL layer is selectively formed through an ink jet method in an atmosphere comprising nitrogen,

wherein the insulating film is capable of preventing penetration of alkaline metal.

5. (Amended) A method for manufacturing an electrical device comprising the steps of:

- forming at least a thin film transistor on an insulating surface;
- forming an insulating film over the thin film transistor;
- forming a pixel electrode over the insulating film, said pixel electrode being connected to the thin film transistor;
- forming an EL layer over the pixel electrode;
- forming a second electrode over the EL layer,

wherein the EL layer is selectively formed through an ink jet method in an atmosphere comprising argon,

wherein the insulating film is capable of preventing penetration of [an] alkaline metal.

7. (Amended) A method according to claim 1, wherein an organic resin film is formed the thin film transistor and the insulating film.

10. (Amended) A method according to claim 4, wherein an organic resin film is formed between the thin film transistor and the insulating film.

21. (Amended) A method according to claim 5, wherein an organic resin is formed between the thin film transistor and the insulating film.

30. (Amended) A method according to claim 1, wherein one of the pixel electrode and the second electrode comprises at least one selected from the group consisting of magnesium (Mg), lithium (Li), cesium (Cs), barium (Ba), potassium (K), beryllium (Be), and calcium (Ca).

31. (Amended) A method according to claim 1, wherein the insulating film comprises at least one selected from the group consisting of silicon nitride oxide and silicon nitride.

32. (Amended) A method according to claim 2, wherein an organic resin is formed between the thin film transistor and the insulating film.

33. (Amended) A method according to claim 2, wherein one of the pixel electrode and the second electrode comprises at least one selected from the group

consisting of magnesium (Mg), lithium (Li), cesium (Cs), barium (Ba), potassium (K), beryllium (Be), and calcium (Ca).

34. (Amended) A method according to claim 2, wherein the insulating film comprises aluminum nitride.

35. (Amended) A method according to claim 3, wherein an organic resin is formed between the thin film transistor and the insulating film.

Please add new claims 36-40 as follows.

--36. (New) A method according to claim 3, wherein one of the pixel electrode and the second electrode comprises at least one selected from the group consisting of magnesium (Mg), lithium (Li), cesium (Cs), barium (Ba), potassium (K), beryllium (Be), and calcium (Ca).

37. (New) A method according to claim 4, wherein one of the pixel electrode and the second electrode comprises at least one selected from the group consisting of magnesium (Mg), lithium (Li), cesium (Cs), barium (Ba), potassium (K), beryllium (Be), and calcium (Ca).

38. (New) A method according to claim 4, wherein the atmosphere is a dry nitrogen atmosphere.

39. (New) A method according to claim 5, wherein one of the pixel electrode and the second electrode comprises at least one selected from the group consisting of magnesium (Mg), lithium (Li), cesium (Cs), barium (Ba), potassium (K), beryllium (Be), and calcium (Ca).